

N-channel 600 V, 0.278 Ω typ., 9 A MDmesh™ M2 Power MOSFET in a PowerFLAT™ 5x6 HV package

Datasheet - production data

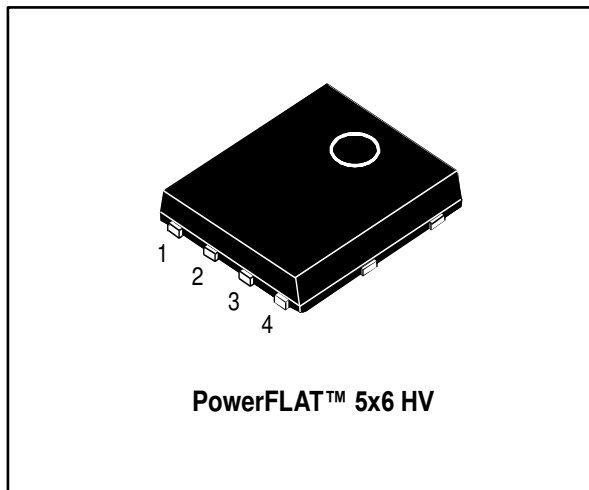


Figure 1: Internal schematic diagram

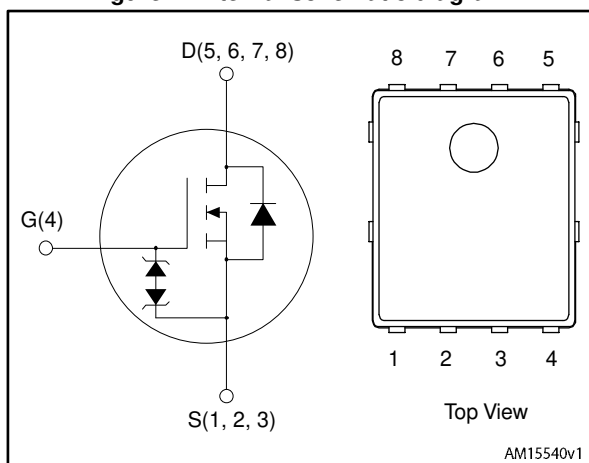


Table 1: Device summary

Order code	Marking	Package	Packing
STL18N60M2	18N60M2	PowerFLAT™ 5x6 HV	Tape and reel

Features

Order code	V _{DS} @ T _{Jmax}	R _{DS(on)} max.	I _D
STL18N60M2	650 V	0.308 Ω	9 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	9	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	5.5	A
$I_{DM}^{(2)}$	Drain current (pulsed)	36	A
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	57	W
I_{AR}	Avalanche current, repetitive or notrepetitive (pulse width limited by T_j max)	2	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	135	mJ
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	- 55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

Notes:

⁽¹⁾The value is limited by package.

⁽²⁾Pulse width limited by safe operating area.

⁽³⁾ $I_{SD} \leq 9\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS(peak)} \leq V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.

⁽⁴⁾ $V_{DS} \leq 480\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.2	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	59	$^\circ\text{C}/\text{W}$

Notes:

⁽¹⁾When mounted on 1inch² FR-4 board, 2 oz Cu.

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 1 mA	600			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 600 V			1	μA
		V _{GS} = 0 V, V _{DS} = 600 V, T _C = 125 °C ⁽¹⁾			100	μA
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±25 V			10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 4.5 A		0.278	0.308	Ω

Notes:

⁽¹⁾ Defined by design, not subject to production test.

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0 V	-	791	-	pF
C _{oss}	Output capacitance		-	40	-	pF
C _{rss}	Reverse transfer capacitance			1.3	-	pF
C _{oss eq.} ⁽¹⁾	Output equivalent capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V	-	164.5	-	pF
R _G	Intrinsic gate resistance	f = 1 MHz, I _D = 0 A	-	5.6	-	Ω
Q _g	Total gate charge	V _{DD} = 480 V, I _D = 13 A, V _{GS} = 0 to 10 V (see Figure 15: "Test circuit for gate charge behavior")	-	21.5	-	nC
Q _{gs}	Gate-source charge		-	3.2	-	nC
Q _{gd}	Gate-drain charge		-	11.3	-	nC

Notes:

⁽¹⁾C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80 % V_{DS}.

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 300 V, I _D = 6.5 A R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 14: "Test circuit for resistive load switching times" and Figure 19: "Switching time waveform")	-	12	-	ns
t _r	Rise time		-	9	-	ns
t _{d(off)}	Turn-off delay time		-	47	-	ns
t _f	Fall time		-	10.6	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 13\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 13\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	305		ns
Q_{rr}	Reverse recovery charge		-	3.3		μC
I_{RRM}	Reverse recovery current		-	22		A
t_{rr}	Reverse recovery time	$I_{SD} = 13\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	417		ns
Q_{rr}	Reverse recovery charge		-	4.6		μC
I_{RRM}	Reverse recovery current		-	22.2		A

Notes:

⁽¹⁾Pulse width is limited by safe operating area.

⁽²⁾Pulse test: pulse duration = 300 μs , duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

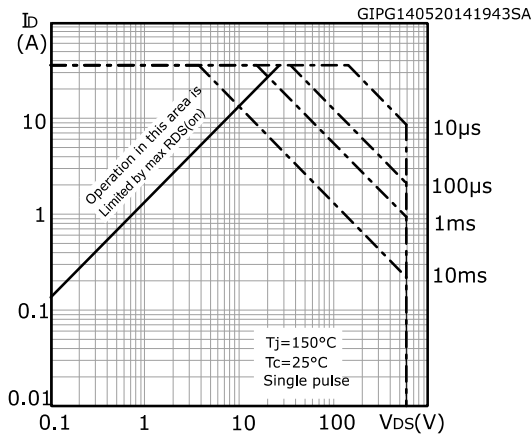


Figure 3: Thermal impedance

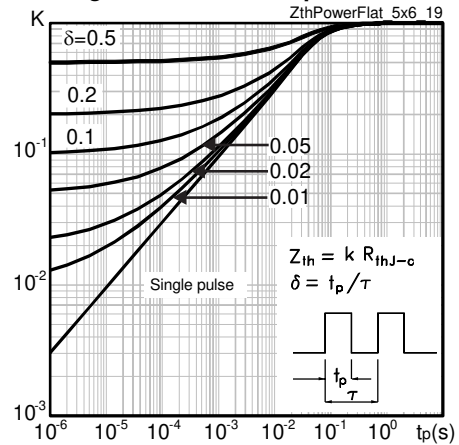


Figure 4: Output characteristics

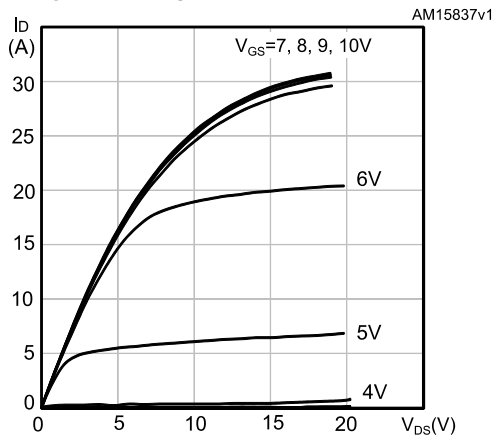


Figure 5: Transfer characteristics

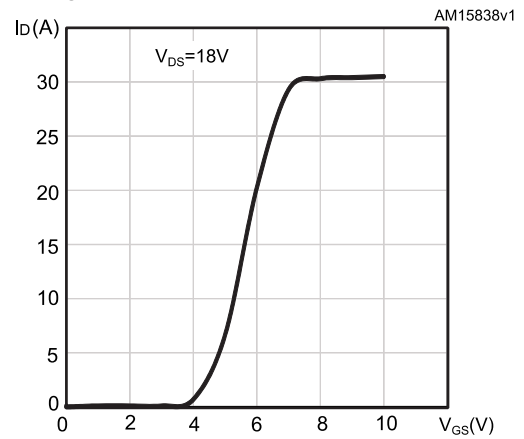


Figure 6: Gate charge vs gate-source voltage

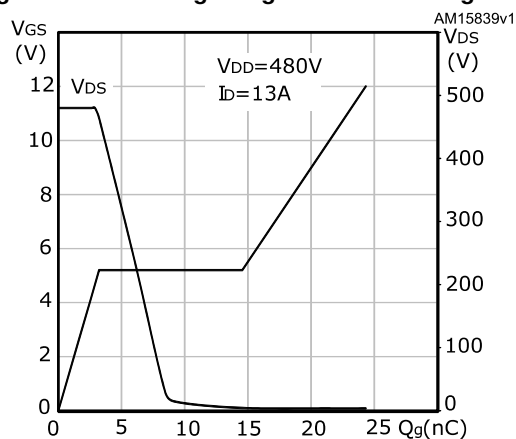


Figure 7: Static drain-source on-resistance

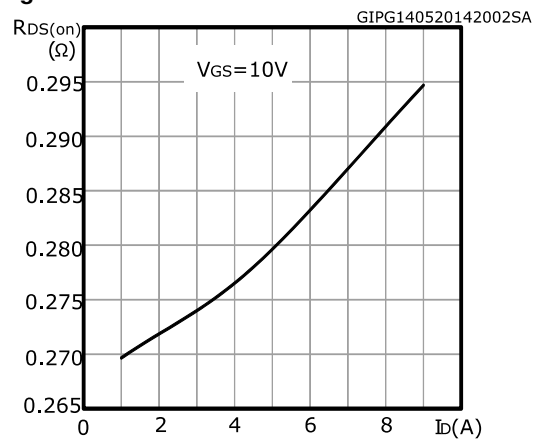


Figure 8: Capacitance variations

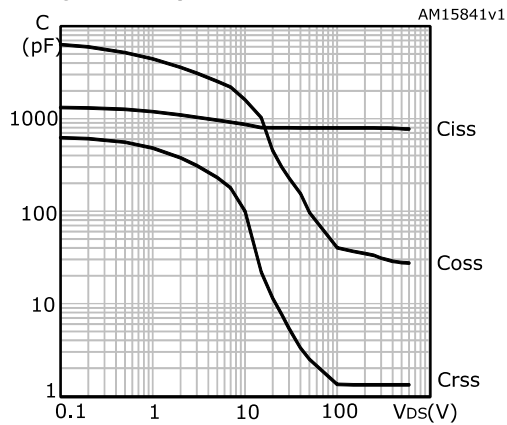


Figure 9: Output capacitance stored energy

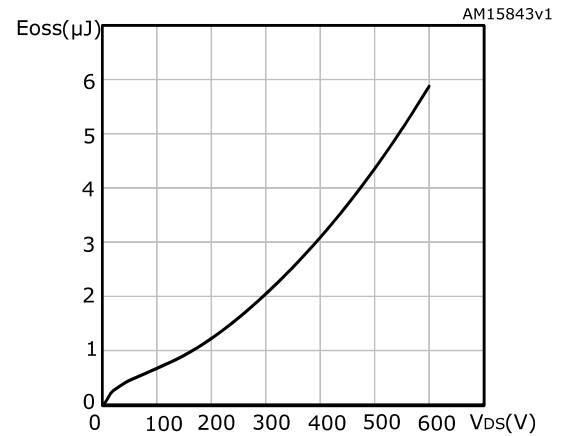


Figure 10: Normalized gate threshold voltage vs temperature

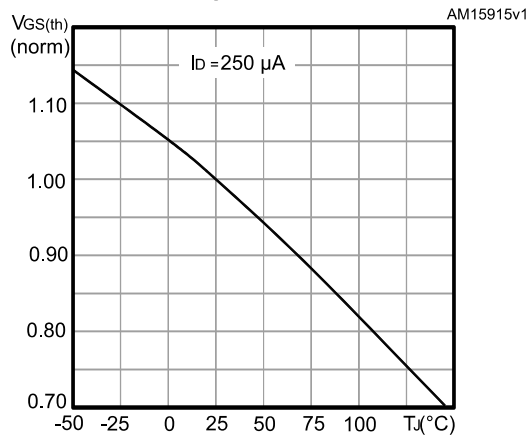


Figure 11: Normalized on-resistance vs temperature

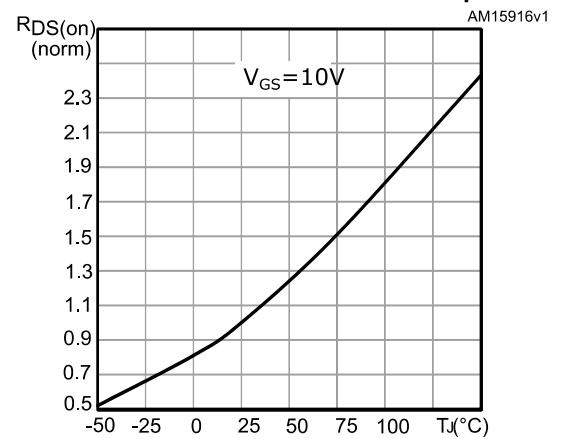


Figure 12: Normalized V(BR)DSS vs temperature

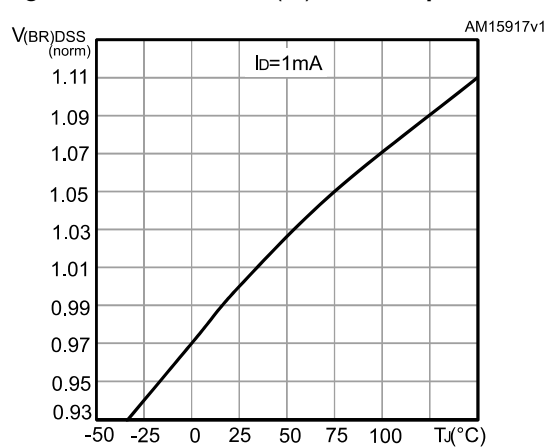
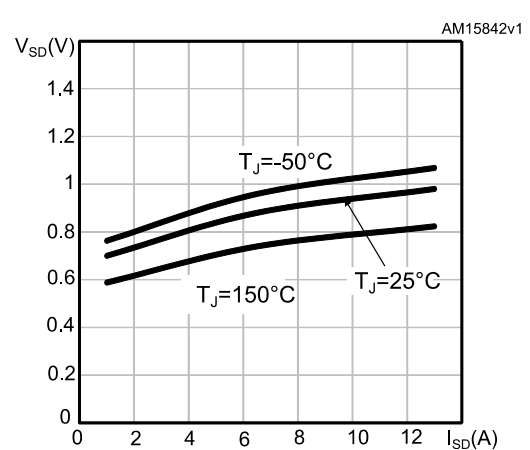
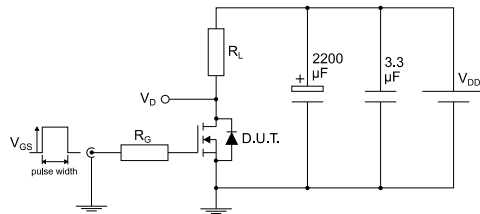


Figure 13: Source-drain diode forward characteristics



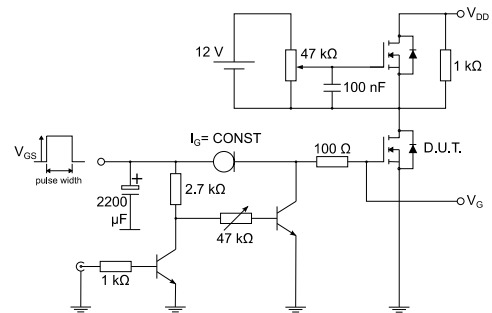
3 Test circuits

Figure 14: Test circuit for resistive load switching times



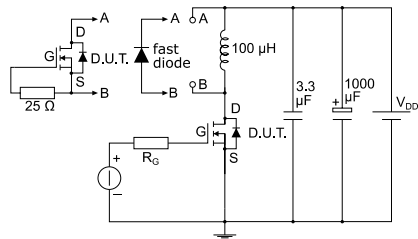
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Figure 15: Test circuit for gate charge behavior



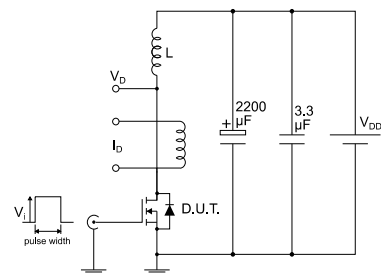
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Figure 16: Test circuit for inductive load switching and diode recovery times



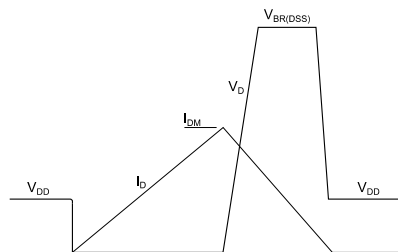
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Figure 17: Unclamped inductive load test circuit



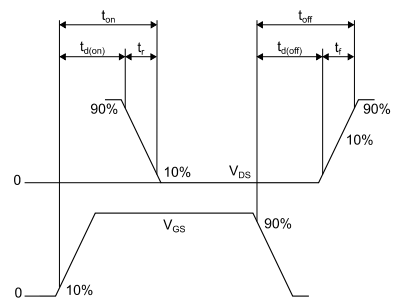
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Figure 18: Unclamped inductive waveform



AM01472v1

Figure 19: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 5x6 HV package information

Figure 20: PowerFLAT™ 5x6 HV package outline

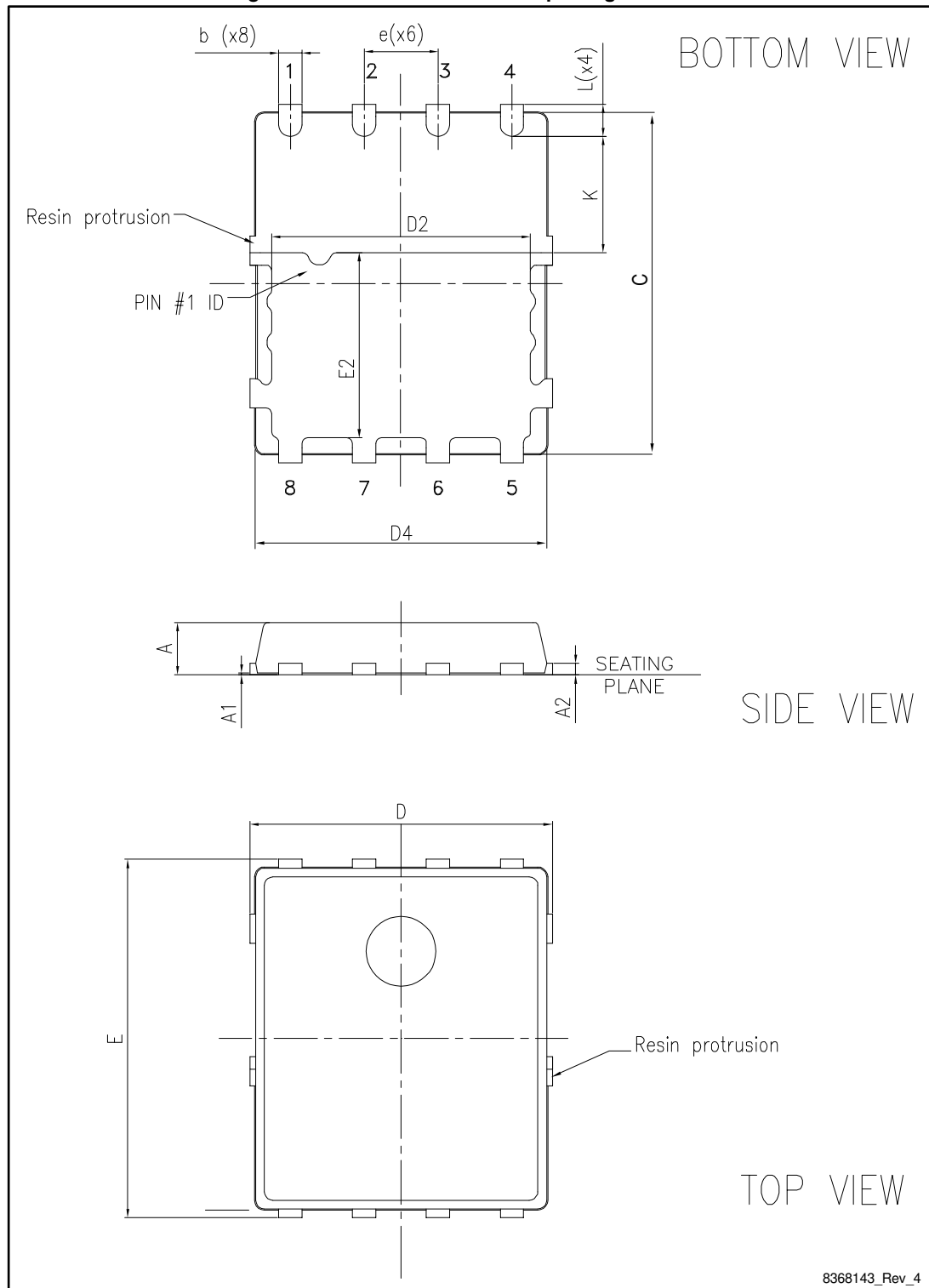
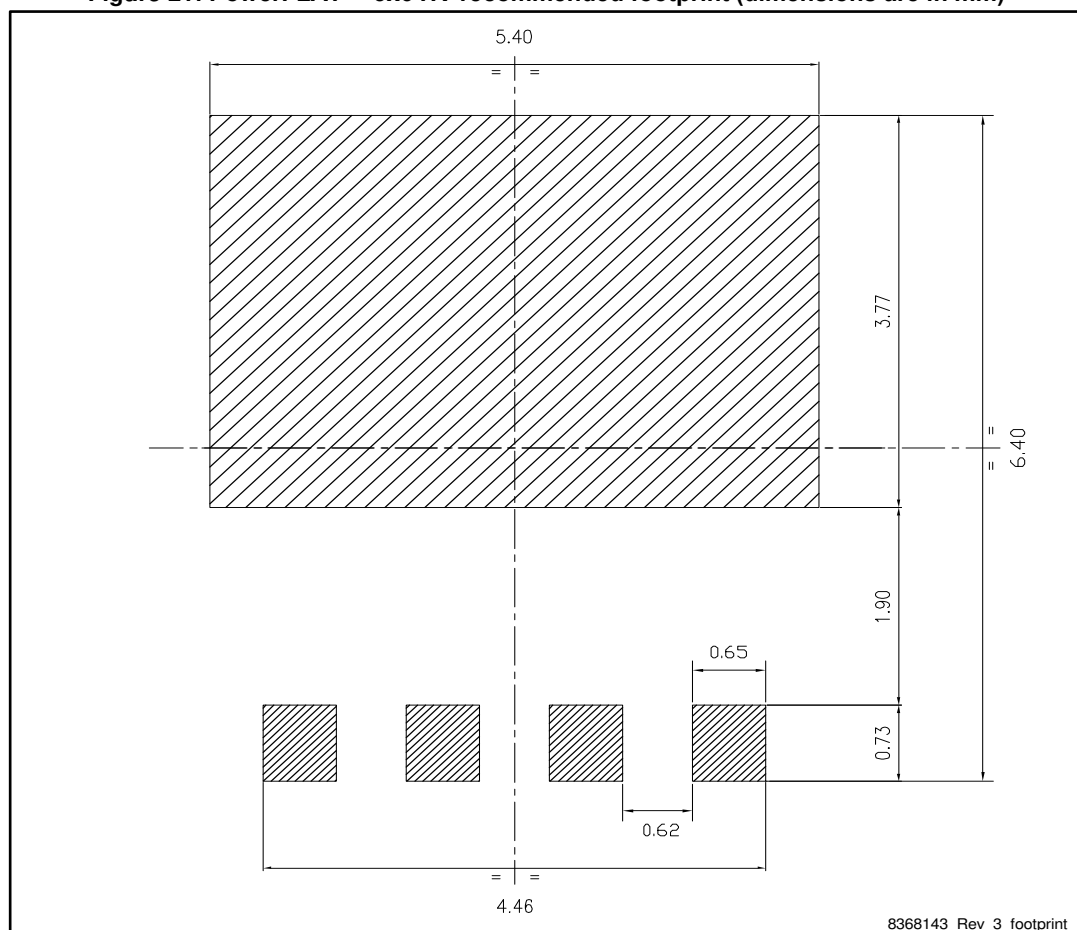


Table 8: PowerFLAT™ 5x6 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.8	6	6.1
D	5.10	5.20	5.30
E	6.05	6.15	6.25
E2	3.10	3.20	3.30
D2	4.30	4.40	4.50
D4	4.8	5	5.1
e		1.27	
L	0.50	0.55	0.60
K	1.90	2.00	2.10

Figure 21: PowerFLAT™ 5x6 HV recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 packing information

Figure 22: PowerFLAT™ 5x6 tape (dimensions are in mm)

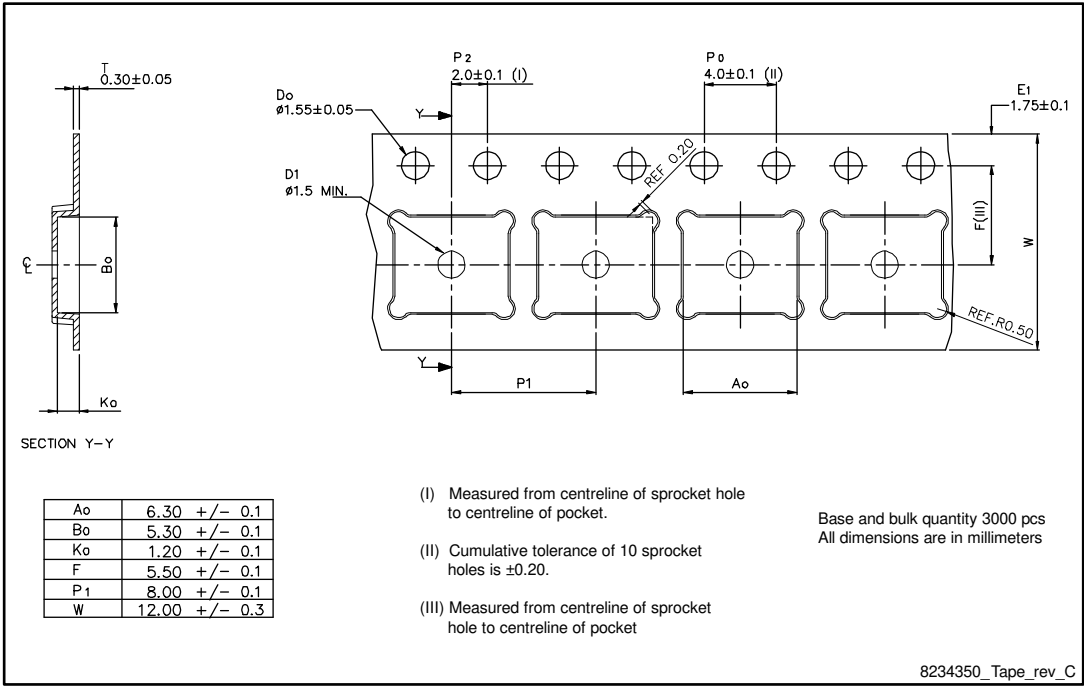


Figure 23: PowerFLAT™ 5x6 package orientation in carrier tape

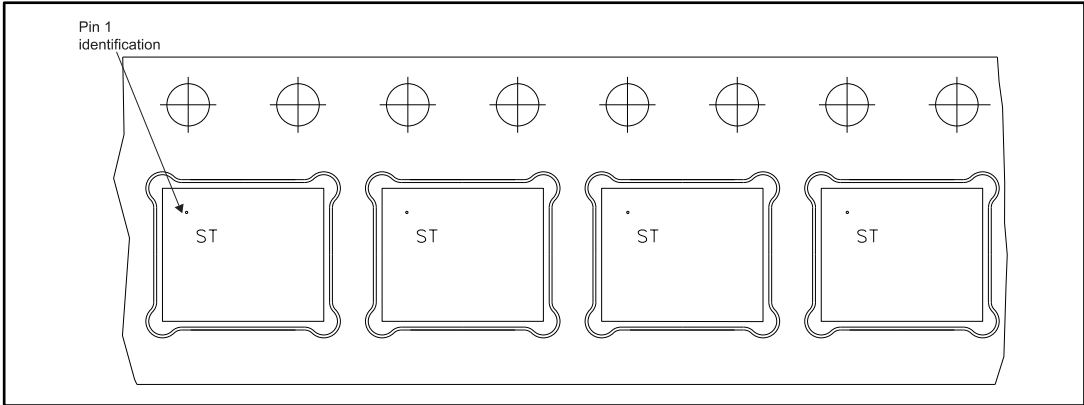
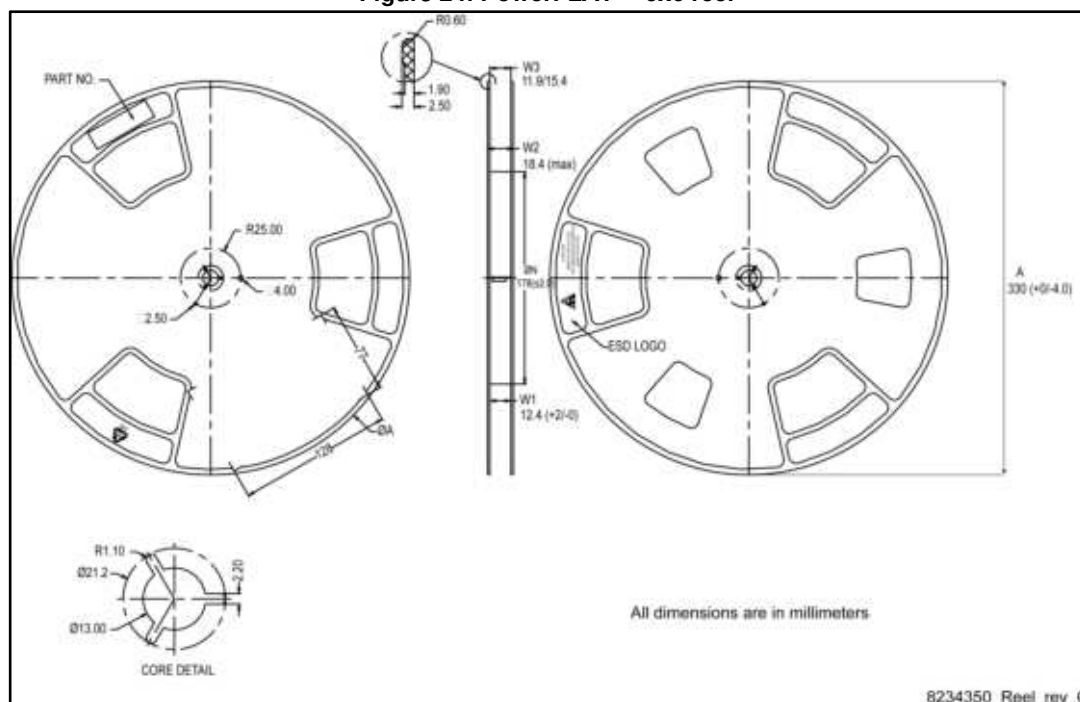


Figure 24: PowerFLAT™ 5x6 reel



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
12-Jun-2014	1	First release.
02-Aug-2017	2	Updated title, features and description in cover page. Updated Table 4: "On/off states" , Figure 3: "Thermal impedance" , Figure 11: "Normalized on-resistance vs temperature" and Section 4: "Package information" . Minor text changes.

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